

2.5 V/3.3 V ECL 1:2 Differential Fanout Buffer MC10LVEP11, MC100LVEP11

Description

The MC10/100LVEP11 is a differential 1:2 fanout buffer. The device is pin and functionally equivalent to the EP11 device. With AC performance the same as the EP11 device, the LVEP11 is ideal for applications requiring lower voltage. Single-ended CLK input operation is limited to a $V_{CC} \geq 3.0$ V in PECL mode, or $V_{EE} \leq -3.0$ V in NECL mode.

The 100 Series contains temperature compensation.

Features

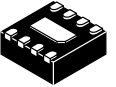
- 240 ps Typical Propagation Delay
- Maximum Frequency > 3.0 GHz Typical
- PECL Mode Operating Range:
 - ♦ $V_{CC} = 2.375$ V to 3.8 V with $V_{EE} = 0$ V
- NECL Mode Operating Range:
 - ♦ $V_{CC} = 0$ V with $V_{EE} = -2.375$ V to -3.8 V
- Open Input Default State
- Q Output Will Default LOW with Inputs Open or at V_{EE}
- LVDS Input Compatible
- These Devices are Pb-Free, Halogen Free and are RoHS Compliant



SOIC-8 NB
D SUFFIX
CASE
751-07

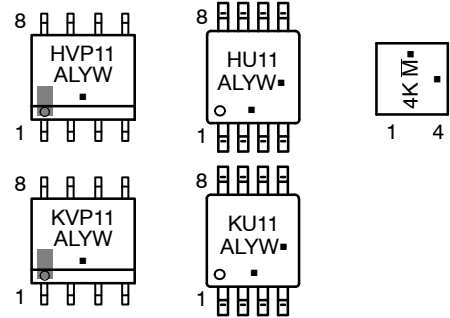


TSSOP-8
DT SUFFIX
CASE
948R-02



DFN-8
MN SUFFIX
CASE 506AA

MARKING DIAGRAM



H = MC10 L = Wafer Lot
K = MC100 Y = Year
4K = MC100 W = Work Week
M = Date Code ▣ = Pb-Free Package
A = Assembly Location

(Note: Microdot may be in either location)
*For additional marking information, refer to Application Note [AND8002/D](#).

ORDERING INFORMATION

Device	Package	Shipping [†]
MC10LVEP11DR2G	SOIC-8 NB (Pb-Free)	2500 / Tape & Reel
MC10LVEP11DTG	TSSOP-8 (Pb-Free)	100 Units / Tube
MC100LVEP11DG	SOIC-8 NB (Pb-Free)	98 Units / Tube
MC100LVEP11DR2G	SOIC-8 NB (Pb-Free)	2500 / Tape & Reel
MC100LVEP11DTG	TSSOP-8 (Pb-Free)	100 Units / Tube
MC100LVEP11DTR2G	TSSOP-8 (Pb-Free)	2500 / Tape & Reel
MC100LVEP11MNR4G	DFN-8 (Pb-Free)	1000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, [BRD8011/D](#).

MC10LVEP11, MC100LVEP11

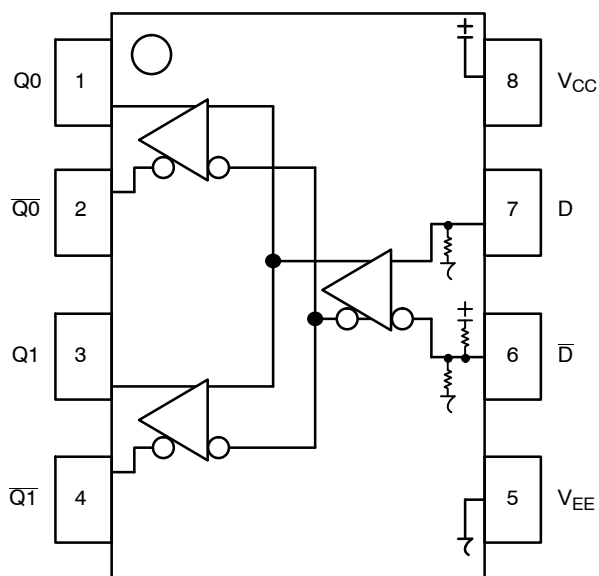


Figure 1. 8-Lead Pinout (Top View) and Logic Diagram

Table 1. PIN DESCRIPTION

PIN	FUNCTION
D*, $\bar{D}^{**}$	ECL Data Inputs
Q0, $\bar{Q}0$, Q1, $\bar{Q}1$	ECL Data Outputs
V _{CC}	Positive Supply
V _{EE}	Negative Supply
EP	(DFN-8 only) Thermal exposed pad must be connected to a sufficient thermal conduit. Electrically connect to the most negative supply (GND) or leave unconnected, floating open.

*Pins will default to 2/3 V_{CC} when left open.

**Pins will default LOW when left open.

Table 2. ATTRIBUTES

Characteristics	Value
Internal Input Pulldown Resistor	75 kΩ
Internal Input Pullup Resistor	37.5 kΩ
ESD Protection Human Body Model Machine Model Charged Device Model	> 4 kV > 200 V > 2 kV
Moisture Sensitivity, Indefinite Time Out of Drypack (Note 1)	Pb-Free Pkg
SOIC-8 NB TSSOP-8 DFN-8	Level 1 Level 3 Level 1
Flammability Rating Oxygen Index: 28 to 34	UL 94 V-0 @ 0.125 in
Transistor Count	110 Devices
Meets or exceeds JEDEC Spec EIA/JESD78 IC Latchup Test	

1. For additional information, see Application Note [AND8003/D](#).

MC10LVEP11, MC100LVEP11

Table 3. MAXIMUM RATINGS

Symbol	Parameter	Condition 1	Condition 2	Rating	Unit
V_{CC}	PECL Mode Power Supply	$V_{EE} = 0\text{ V}$		6	V
V_{EE}	NECL Mode Power Supply	$V_{CC} = 0\text{ V}$		-6	V
V_I	PECL Mode Input Voltage NECL Mode Input Voltage	$V_{EE} = 0\text{ V}$ $V_{CC} = 0\text{ V}$	$V_I \leq V_{CC}$ $V_I \geq V_{EE}$	6 -6	V
I_{out}	Output Current	Continuous Surge		50 100	mA
T_A	Operating Temperature Range			-40 to +85	°C
T_{stg}	Storage Temperature Range			-65 to +150	°C
θ_{JA}	Thermal Resistance (Junction-to-Ambient)	0 lfpm 500 lfpm	SOIC-8 NB	190 130	°C/W
θ_{JC}	Thermal Resistance (Junction-to-Case)	Standard Board	SOIC-8 NB	41 to 44	°C/W
θ_{JA}	Thermal Resistance (Junction-to-Ambient)	0 lfpm 500 lfpm	TSSOP-8	185 140	°C/W
θ_{JC}	Thermal Resistance (Junction-to-Case)	Standard Board	TSSOP-8	41 to 44	°C/W
θ_{JA}	Thermal Resistance (Junction-to-Ambient)	0 lfpm 500 lfpm	DFN-8	129 84	°C/W
θ_{JC}	Thermal Resistance (Junction-to-Case)	(Note 1)	DFN-8	35 to 40	°C/W
T_{sol}	Wave Solder (Pb-Free)	<2 to 3 sec @ 260°C		265	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. JEDEC standard multilayer board – 2S2P (2 signal, 2 power).

MC10LVEP11, MC100LVEP11

Table 4. 10LVEP DC CHARACTERISTICS, PECL ($V_{CC} = 2.5\text{ V}$, $V_{EE} = 0\text{ V}$ (Note 1))

Symbol	Characteristic	-40°C			25°C			85°C			Unit
		Min	Typ	Max	Min	Typ	Max	Min	Typ	Max	
I_{EE}	Power Supply Current	25	33	40	29	33	40	32	34	42	mA
V_{OH}	Output HIGH Voltage (Note 2)	1365	1490	1615	1430	1555	1680	1490	1615	1740	mV
V_{OL}	Output LOW Voltage (Note 2)	565	740	865	630	805	930	690	865	990	mV
V_{IHCMR}	Input HIGH Voltage Common Mode Range (Differential Configuration) (Note 3)	1.2		2.5	1.2		2.5	1.2		2.5	V
I_{IH}	Input HIGH Current			150			150			150	μA
I_{IL}	Input LOW Current D D	0.5 -150			0.5 -150			0.5 -150			μA

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfpm.

1. Input and output parameters vary 1:1 with V_{CC} . V_{EE} can vary +0.125 V to -1.3 V.
2. All loading with 50 Ω to $V_{CC} - 2.0\text{ V}$.
3. V_{IHCMR} min varies 1:1 with V_{EE} , V_{IHCMR} max varies 1:1 with V_{CC} . The V_{IHCMR} range is referenced to the most positive side of the differential input signal. Single-Ended input CLK pin operation is limited to $V_{CC} \geq 3.0\text{ V}$ in PECL mode.

Table 5. 10LVEP DC CHARACTERISTICS, PECL ($V_{CC} = 3.3\text{ V}$, $V_{EE} = 0\text{ V}$ (Note 1))

Symbol	Characteristic	-40°C			25°C			85°C			Unit
		Min	Typ	Max	Min	Typ	Max	Min	Typ	Max	
I_{EE}	Power Supply Current	25	33	40	29	33	40	32	34	42	mA
V_{OH}	Output HIGH Voltage (Note 2)	2165	2290	2415	2230	2355	2480	2290	2415	2540	mV
V_{OL}	Output LOW Voltage (Note 2)	1365	1540	1665	1430	1605	1730	1490	1665	1790	mV
V_{IH}	Input HIGH Voltage (Single-Ended) (Note 3)	2090		2415	2155		2480	2215		2540	mV
V_{IL}	Input LOW Voltage (Single-Ended) (Note 3)	1365		1690	1430		1755	1490		1815	mV
V_{IHCMR}	Input HIGH Voltage Common Mode Range (Differential Configuration) (Note 4)	1.2		3.3	1.2		3.3	1.2		3.3	V
I_{IH}	Input HIGH Current			150			150			150	μA
I_{IL}	Input LOW Current D D	0.5 -150			0.5 -150			0.5 -150			μA

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfpm.

1. Input and output parameters vary 1:1 with V_{CC} . V_{EE} can vary +0.925 V to -0.5 V.
2. All loading with 50 Ω to $V_{CC} - 2.0\text{ V}$.
3. Single-Ended input CLK pin operation is limited to $V_{CC} \geq 3.0\text{ V}$ in PECL mode.
4. V_{IHCMR} min varies 1:1 with V_{EE} , V_{IHCMR} max varies 1:1 with V_{CC} . The V_{IHCMR} range is referenced to the most positive side of the differential input signal.

MC10LVEP11, MC100LVEP11

Table 6. 10LVEP DC CHARACTERISTICS, NECL ($V_{CC} = 0\text{ V}$, $V_{EE} = -3.8\text{ V}$ to -2.375 V (Note 1))

Symbol	Characteristic	-40°C			25°C			85°C			Unit
		Min	Typ	Max	Min	Typ	Max	Min	Typ	Max	
I_{EE}	Power Supply Current	25	33	40	29	33	40	32	34	42	mA
V_{OH}	Output HIGH Voltage (Note 2)	-1135	-1010	-885	-1070	-945	-820	-1010	-885	-760	mV
V_{OL}	Output LOW Voltage (Note 2)	-1935	-1760	-1635	-1870	-1695	-1570	-1810	-1635	-1510	mV
V_{IH}	Input HIGH Voltage (Single-Ended) (Note 3)	-1210		-885	-1145		-820	-1085		-760	mV
V_{IL}	Input LOW Voltage (Single-Ended) (Note 3)	-1935		-1610	-1870		-1545	-1810		-1485	mV
V_{IHCMR}	Input HIGH Voltage Common Mode Range (Differential Configuration) (Note 4)	$V_{EE}+1.2$		0.0	$V_{EE}+1.2$		0.0	$V_{EE}+1.2$		0.0	V
I_{IH}	Input HIGH Current			150			150			150	μA
I_{IL}	Input LOW Current D D	0.5 -150			0.5 -150			0.5 -150			μA

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfm.

1. Input and output parameters vary 1:1 with V_{CC} .
2. All loading with $50\ \Omega$ to $V_{CC} - 2.0\text{ V}$.
3. Single-Ended input CLK pin operation is limited to $V_{EE} \leq -3.0\text{ V}$ in NECL mode.
4. V_{IHCMR} min varies 1:1 with V_{EE} , V_{IHCMR} max varies 1:1 with V_{CC} . The V_{IHCMR} range is referenced to the most positive side of the differential input signal.

Table 7. 100LVEP DC CHARACTERISTICS, PECL ($V_{CC} = 2.5\text{ V}$, $V_{EE} = 0\text{ V}$ (Note 1))

Symbol	Characteristic	-40°C			25°C			85°C			Unit
		Min	Typ	Max	Min	Typ	Max	Min	Typ	Max	
I_{EE}	Power Supply Current	25	35	42	29	38	46	32	41	50	mA
V_{OH}	Output HIGH Voltage (Note 2)	1355	1480	1605	1355	1480	1605	1355	1480	1605	mV
V_{OL}	Output LOW Voltage (Note 2)	555	730	900	555	730	900	555	730	900	mV
V_{IH}	Input HIGH Voltage (Single-Ended)	1335		1620	1335		1620	1335		1620	mV
V_{IL}	Input LOW Voltage (Single-Ended)	555		900	555		900	555		900	mV
V_{IHCMR}	Input HIGH Voltage Common Mode Range (Differential Configuration) (Note 3)	1.2		2.5	1.2		2.5	1.2		2.5	V
I_{IH}	Input HIGH Current			150			150			150	μA
I_{IL}	Input LOW Current D D	0.5 -150			0.5 -150			0.5 -150			μA

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfm.

1. Input and output parameters vary 1:1 with V_{CC} . V_{EE} can vary $+0.125\text{ V}$ to -1.3 V .
2. All loading with $50\ \Omega$ to $V_{CC} - 2.0\text{ V}$.
3. V_{IHCMR} min varies 1:1 with V_{EE} , V_{IHCMR} max varies 1:1 with V_{CC} . The V_{IHCMR} range is referenced to the most positive side of the differential input signal. Single-Ended input CLK pin operation is limited to $V_{CC} \geq 3.0\text{ V}$ in PECL mode.

MC10LVEP11, MC100LVEP11

Table 8. 100LVEP DC CHARACTERISTICS, PECL ($V_{CC} = 3.3\text{ V}$, $V_{EE} = 0\text{ V}$ (Note 1))

Symbol	Characteristic	-40°C			25°C			85°C			Unit
		Min	Typ	Max	Min	Typ	Max	Min	Typ	Max	
I_{EE}	Power Supply Current	25	35	42	29	38	46	32	41	50	mA
V_{OH}	Output HIGH Voltage (Note 2)	2155	2280	2405	2155	2280	2405	2155	2280	2405	mV
V_{OL}	Output LOW Voltage (Note 2)	1355	1530	1700	1355	1530	1700	1355	1530	1700	mV
V_{IH}	Input HIGH Voltage (Single-Ended) (Note 3)	2135		2420	2135		2420	2135		2420	mV
V_{IL}	Input LOW Voltage (Single-Ended) (Note 3)	1355		1700	1355		1700	1355		1700	mV
V_{IHCMR}	Input HIGH Voltage Common Mode Range (Differential Configuration) (Note 4)	1.2		3.3	1.2		3.3	1.2		3.3	V
I_{IH}	Input HIGH Current			150			150			150	μA
I_{IL}	Input LOW Current D D	0.5 -150			0.5 -150			0.5 -150			μA

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfm.

1. Input and output parameters vary 1:1 with V_{CC} . V_{EE} can vary +0.925 V to -0.5 V.
2. All loading with 50 Ω to $V_{CC} - 2.0\text{ V}$.
3. Single-Ended input CLK pin operation is limited to $V_{CC} \geq 3.0\text{ V}$ in PECL mode.
4. V_{IHCMR} min varies 1:1 with V_{EE} . V_{IHCMR} max varies 1:1 with V_{CC} . The V_{IHCMR} range is referenced to the most positive side of the differential input signal.

Table 9. 100LVEP DC CHARACTERISTICS, NECL ($V_{CC} = 0\text{ V}$; $V_{EE} = -3.8\text{ V}$ to -2.375 V (Note 1))

Symbol	Characteristic	-40°C			25°C			85°C			Unit
		Min	Typ	Max	Min	Typ	Max	Min	Typ	Max	
I_{EE}	Power Supply Current	25	35	42	29	38	46	32	41	50	mA
V_{OH}	Output HIGH Voltage (Note 2)	-1145	-1020	-895	-1145	-1020	-895	-1145	-1020	-895	mV
V_{OL}	Output LOW Voltage (Note 2)	-1945	-1770	-1600	-1945	-1770	-1600	-1945	-1770	-1600	mV
V_{IH}	Input HIGH Voltage (Single-Ended) (Note 3)	-1165		-880	-1165		-880	-1165		-880	mV
V_{IL}	Input LOW Voltage (Single-Ended) (Note 3)	-1945	-1425	-1600	-1945	-1425	-1600	-1945	-1425	-1600	mV
V_{IHCMR}	Input HIGH Voltage Common Mode Range (Differential Configuration) (Note 4)	$V_{EE}+1.2$		0.0	$V_{EE}+1.2$		0.0	$V_{EE}+1.2$		0.0	V
I_{IH}	Input HIGH Current			150			150			150	μA
I_{IL}	Input LOW Current D D	0.5 -150			0.5 -150			0.5 -150			μA

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfm.

1. Input and output parameters vary 1:1 with V_{CC} .
2. All loading with 50 Ω to $V_{CC} - 2.0\text{ V}$.
3. Single-Ended input CLK pin operation is limited to $V_{EE} \leq -3.0\text{ V}$ in NECL mode.
4. V_{IHCMR} min varies 1:1 with V_{EE} . V_{IHCMR} max varies 1:1 with V_{CC} . The V_{IHCMR} range is referenced to the most positive side of the differential input signal.

MC10LVEP11, MC100LVEP11

Table 10. AC CHARACTERISTICS ($V_{CC} = 0\text{ V}$; $V_{EE} = -3.8\text{ V}$ to -2.375 V or $V_{CC} = 2.375\text{ V}$ to 3.8 V ; $V_{EE} = 0\text{ V}$ (Note 1))

Symbol	Characteristic	-40°C			25°C			85°C			Unit
		Min	Typ	Max	Min	Typ	Max	Min	Typ	Max	
$f_{\max}$	Maximum Frequency (Figure 2)		3			3			3		GHz
t_{PLH} , t_{PHL}	Propagation Delay (Differential Configuration) CLK to Q, $\bar{Q}$	170	230	300	180	240	310	210	270	360	ps
t_{SKEW}	Within Device Skew Q, $\bar{Q}$ Device to Device Skew (Note 2)		5.0	20 130		5.0	20 130		5.0	20 150	ps
t_{JITTER}	CLOCK Random Jitter (RMS) @ $\leq 1.0\text{ GHz}$ @ $\leq 1.5\text{ GHz}$ @ $\leq 2.0\text{ GHz}$ @ $\leq 2.5\text{ GHz}$ @ $\leq 3.0\text{ GHz}$		0.126 0.112 0.111 0.112 0.155	0.3 0.2 0.3 0.2 0.2		0.142 0.162 0.122 0.172 0.217	0.4 0.3 0.2 0.3 0.3		0.209 0.162 0.170 0.235 0.368	0.3 0.2 0.3 0.3 0.6	ps
V_{PP}	Input Voltage Swing (Differential Configuration)	150	800	1200	150	800	1200	150	800	1200	mV
t_r t_f	Output Rise/Fall Times Q, $\bar{Q}$ (20% – 80%)	70	110	170	80	120	180	100	140	200	ps

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfm.

1. Measured using a 750 mV source, 50% duty cycle clock source. All loading with $50\ \Omega$ to $V_{CC} - 2.0\text{ V}$.
2. Skew is measured between outputs under identical transitions.

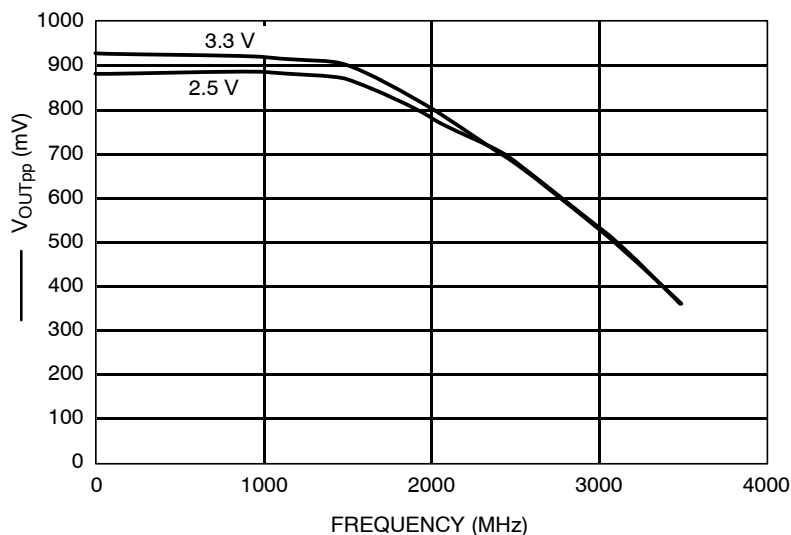


Figure 2. $F_{\max}$ Typical

MC10LVEP11, MC100LVEP11

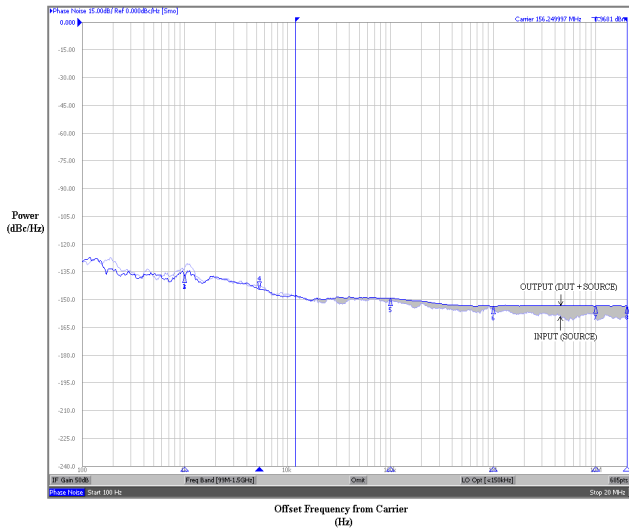


Figure 3. Typical Phase Noise Plot at $f_{\text{carrier}} = 156.25 \text{ MHz}$

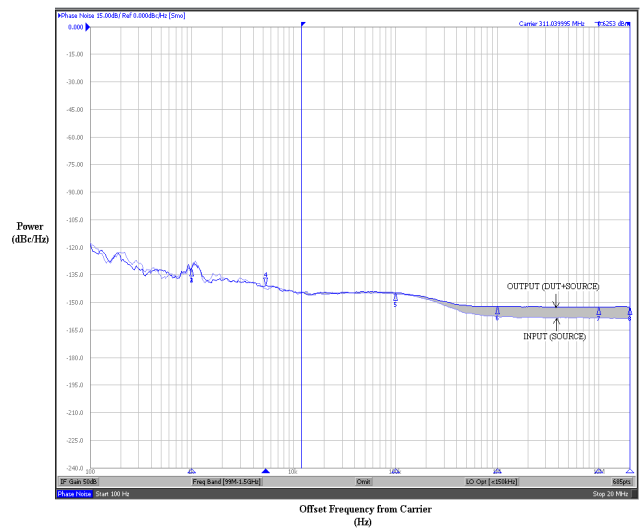


Figure 4. Typical Phase Noise Plot at $f_{\text{carrier}} = 311.04 \text{ MHz}$

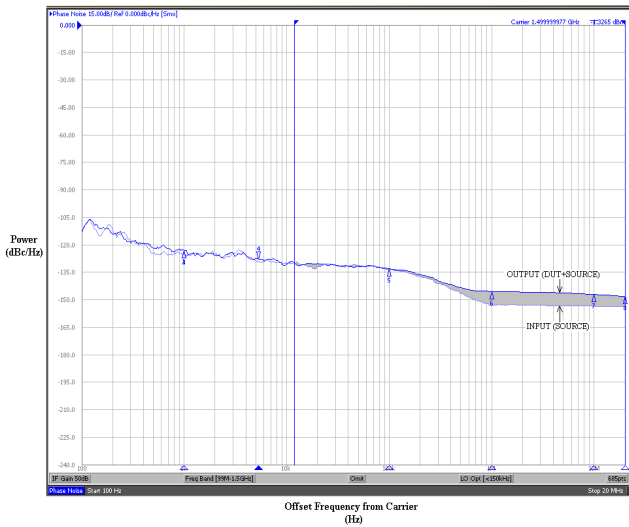


Figure 5. Typical Phase Noise Plot at $f_{\text{carrier}} = 1.5 \text{ GHz}$

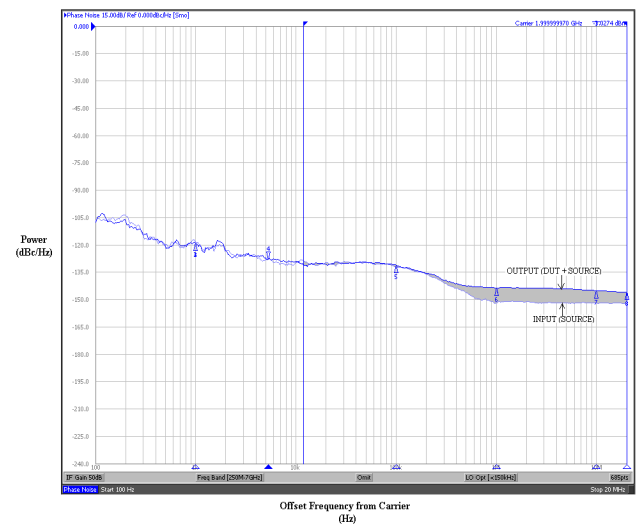


Figure 6. Typical Phase Noise Plot at $f_{\text{carrier}} = 2 \text{ GHz}$

The above phase noise plots captured using Agilent E5052A show additive phase noise of the MC100LVEP11 device at frequencies 156.25 MHz, 311.04 MHz, 1.5 GHz and 2 GHz respectively at an operating voltage of 3.3 V in room temperature. The RMS Phase Jitter contributed by the

device (integrated between 12 kHz and 20 MHz; as shown in the shaded region of the plot) at each of the frequencies is 66 fs, 37 fs, 14 fs and 13 fs respectively. The input source used for the phase noise measurements is Agilent E8663B.

MC10LVEP11, MC100LVEP11

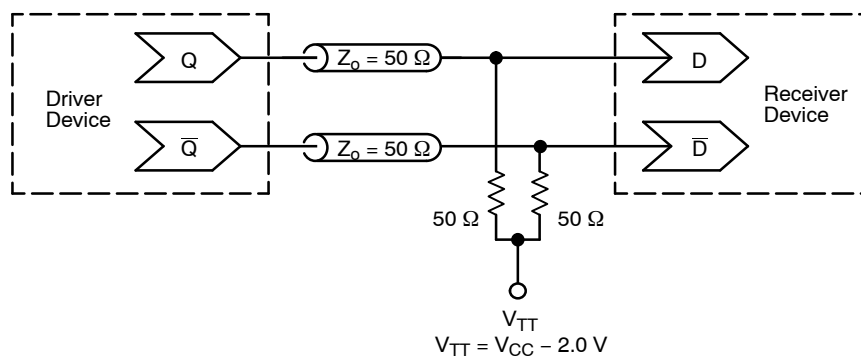
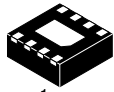


Figure 7. Typical Termination for Output Driver and Device Evaluation
(See Application Note [AND8020/D](#) – Termination of ECL Logic Devices.)

Resource Reference of Application Notes

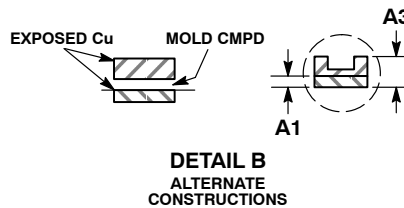
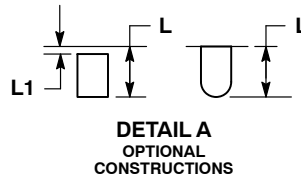
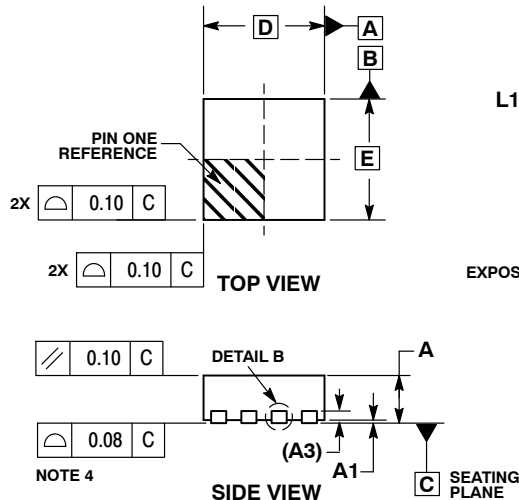
- AN1405/D** – ECL Clock Distribution Techniques
- AN1406/D** – Designing with PECL (ECL at +5.0 V)
- AN1503/D** – ECLinPS™ I/O SPiCE Modeling Kit
- AN1504/D** – Metastability and the ECLinPS Family
- AN1568/D** – Interfacing Between LVDS and ECL
- AN1672/D** – The ECL Translator Guide
- AND8001/D** – Odd Number Counters Design
- AND8002/D** – Marking and Date Codes
- AND8020/D** – Termination of ECL Logic Devices
- AND8066/D** – Interfacing with ECLinPS
- AND8090/D** – AC Characteristics of ECL Devices



SCALE 4:1

DFN8 2x2, 0.5P
CASE 506AA
ISSUE F

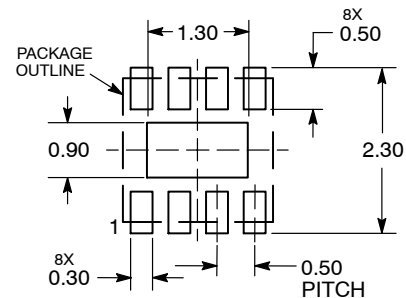
DATE 04 MAY 2016



NOTES:

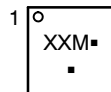
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. DIMENSION b APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN 0.15 AND 0.20 MM FROM TERMINAL TIP.
4. COPLANARITY APPLIES TO THE EXPOSED PAD AS WELL AS THE TERMINALS.

MILLIMETERS		
DIM	MIN	MAX
A	0.80	1.00
A1	0.00	0.05
A3	0.20	REF
b	0.20	0.30
D	2.00	BSC
D2	1.10	1.30
E	2.00	BSC
E2	0.70	0.90
e	0.50	BSC
K	0.30	REF
L	0.25	0.35
L1		0.10

RECOMMENDED SOLDERING FOOTPRINT*


DIMENSIONS: MILLIMETERS

*For additional information on our Pb-Free strategy and soldering details, please download the **onsemi** Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

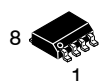
GENERIC MARKING DIAGRAM*


XX = Specific Device Code
M = Date Code
▪ = Pb-Free Device

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

DOCUMENT NUMBER:	98AON18658D	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.
DESCRIPTION:	DFN8, 2.0X2.0, 0.5MM PITCH	PAGE 1 OF 1

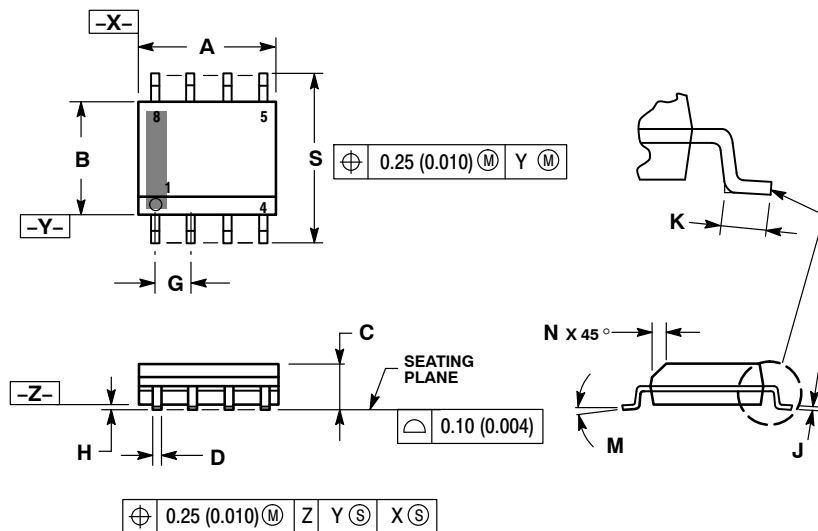
onsemi and onsemi are trademarks of Semiconductor Components Industries, LLC dba onsemi or its subsidiaries in the United States and/or other countries. onsemi reserves the right to make changes without further notice to any products herein. onsemi makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. onsemi does not convey any license under its patent rights nor the rights of others.



SCALE 1:1

SOIC-8 NB
CASE 751-07
ISSUE AK

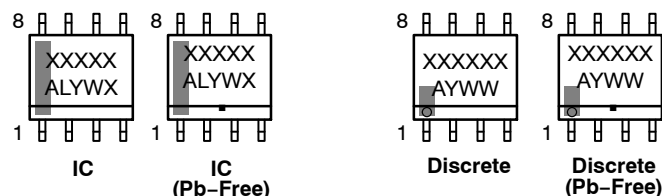
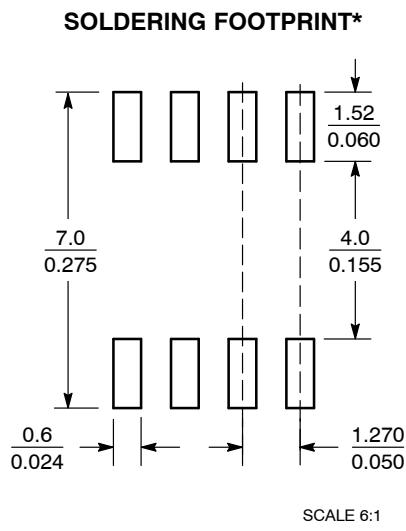
DATE 16 FEB 2011



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION A AND B DO NOT INCLUDE MOLD PROTRUSION.
4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.
6. 751-01 THRU 751-06 ARE OBSOLETE. NEW STANDARD IS 751-07.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.80	5.00	0.189	0.197
B	3.80	4.00	0.150	0.157
C	1.35	1.75	0.053	0.069
D	0.33	0.51	0.013	0.020
G	1.27 BSC		0.050 BSC	
H	0.10	0.25	0.004	0.010
J	0.19	0.25	0.007	0.010
K	0.40	1.27	0.016	0.050
M	0°	8°	0°	8°
N	0.25	0.50	0.010	0.020
S	5.80	6.20	0.228	0.244

GENERIC
MARKING DIAGRAM*


XXXXXX = Specific Device Code
A = Assembly Location
L = Wafer Lot
Y = Year
W = Work Week
▪ = Pb-Free Package

XXXXXX = Specific Device Code
A = Assembly Location
Y = Year
WW = Work Week
▪ = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

*For additional information on our Pb-Free strategy and soldering details, please download the **onsemi** Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

STYLES ON PAGE 2

DOCUMENT NUMBER:	98ASB42564B	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.
DESCRIPTION:	SOIC-8 NB	PAGE 1 OF 2

onsemi and onsemi are trademarks of Semiconductor Components Industries, LLC dba onsemi or its subsidiaries in the United States and/or other countries. onsemi reserves the right to make changes without further notice to any products herein. onsemi makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. onsemi does not convey any license under its patent rights nor the rights of others.

SOIC-8 NB
CASE 751-07
ISSUE AK

DATE 16 FEB 2011

STYLE 1: PIN 1. EMITTER 2. COLLECTOR 3. COLLECTOR 4. EMITTER 5. EMITTER 6. BASE 7. BASE 8. EMITTER	STYLE 2: PIN 1. COLLECTOR, DIE, #1 2. COLLECTOR, #1 3. COLLECTOR, #2 4. COLLECTOR, #2 5. BASE, #2 6. EMITTER, #2 7. BASE, #1 8. EMITTER, #1	STYLE 3: PIN 1. DRAIN, DIE #1 2. DRAIN, #1 3. DRAIN, #2 4. DRAIN, #2 5. GATE, #2 6. SOURCE, #2 7. GATE, #1 8. SOURCE, #1	STYLE 4: PIN 1. ANODE 2. ANODE 3. ANODE 4. ANODE 5. ANODE 6. ANODE 7. ANODE 8. COMMON CATHODE
STYLE 5: PIN 1. DRAIN 2. DRAIN 3. DRAIN 4. DRAIN 5. GATE 6. GATE 7. SOURCE 8. SOURCE	STYLE 6: PIN 1. SOURCE 2. DRAIN 3. DRAIN 4. SOURCE 5. SOURCE 6. GATE 7. GATE 8. SOURCE	STYLE 7: PIN 1. INPUT 2. EXTERNAL BYPASS 3. THIRD STAGE SOURCE 4. GROUND 5. DRAIN 6. GATE 3 7. SECOND STAGE Vd 8. FIRST STAGE Vd	STYLE 8: PIN 1. COLLECTOR, DIE #1 2. BASE, #1 3. BASE, #2 4. COLLECTOR, #2 5. COLLECTOR, #2 6. EMITTER, #2 7. EMITTER, #1 8. COLLECTOR, #1
STYLE 9: PIN 1. EMITTER, COMMON 2. COLLECTOR, DIE #1 3. COLLECTOR, DIE #2 4. EMITTER, COMMON 5. EMITTER, COMMON 6. BASE, DIE #2 7. BASE, DIE #1 8. EMITTER, COMMON	STYLE 10: PIN 1. GROUND 2. BIAS 1 3. OUTPUT 4. GROUND 5. GROUND 6. BIAS 2 7. INPUT 8. GROUND	STYLE 11: PIN 1. SOURCE 1 2. GATE 1 3. SOURCE 2 4. GATE 2 5. DRAIN 2 6. DRAIN 2 7. DRAIN 1 8. DRAIN 1	STYLE 12: PIN 1. SOURCE 2. SOURCE 3. SOURCE 4. GATE 5. DRAIN 6. DRAIN 7. DRAIN 8. DRAIN
STYLE 13: PIN 1. N.C. 2. SOURCE 3. SOURCE 4. GATE 5. DRAIN 6. DRAIN 7. DRAIN 8. DRAIN	STYLE 14: PIN 1. N-SOURCE 2. N-GATE 3. P-SOURCE 4. P-GATE 5. P-DRAIN 6. P-DRAIN 7. N-DRAIN 8. N-DRAIN	STYLE 15: PIN 1. ANODE 1 2. ANODE 1 3. ANODE 1 4. ANODE 1 5. CATHODE, COMMON 6. CATHODE, COMMON 7. CATHODE, COMMON 8. CATHODE, COMMON	STYLE 16: PIN 1. EMITTER, DIE #1 2. BASE, DIE #1 3. EMITTER, DIE #2 4. BASE, DIE #2 5. COLLECTOR, DIE #2 6. COLLECTOR, DIE #2 7. COLLECTOR, DIE #1 8. COLLECTOR, DIE #1
STYLE 17: PIN 1. VCC 2. V2OUT 3. V1OUT 4. TXE 5. RXE 6. VEE 7. GND 8. ACC	STYLE 18: PIN 1. ANODE 2. ANODE 3. SOURCE 4. GATE 5. DRAIN 6. DRAIN 7. CATHODE 8. CATHODE	STYLE 19: PIN 1. SOURCE 1 2. GATE 1 3. SOURCE 2 4. GATE 2 5. DRAIN 2 6. MIRROR 2 7. DRAIN 1 8. MIRROR 1	STYLE 20: PIN 1. SOURCE (N) 2. GATE (N) 3. SOURCE (P) 4. GATE (P) 5. DRAIN 6. DRAIN 7. DRAIN 8. DRAIN
STYLE 21: PIN 1. CATHODE 1 2. CATHODE 2 3. CATHODE 3 4. CATHODE 4 5. CATHODE 5 6. COMMON ANODE 7. COMMON ANODE 8. CATHODE 6	STYLE 22: PIN 1. I/O LINE 1 2. COMMON CATHODE/VCC 3. COMMON CATHODE/VCC 4. I/O LINE 3 5. COMMON ANODE/GND 6. I/O LINE 4 7. I/O LINE 5 8. COMMON ANODE/GND	STYLE 23: PIN 1. LINE 1 IN 2. COMMON ANODE/GND 3. COMMON ANODE/GND 4. LINE 2 IN 5. LINE 2 OUT 6. COMMON ANODE/GND 7. COMMON ANODE/GND 8. LINE 1 OUT	STYLE 24: PIN 1. BASE 2. EMITTER 3. COLLECTOR/ANODE 4. COLLECTOR/ANODE 5. CATHODE 6. CATHODE 7. COLLECTOR/ANODE 8. COLLECTOR/ANODE
STYLE 25: PIN 1. VIN 2. N/C 3. REXT 4. GND 5. IOUT 6. IOUT 7. IOUT 8. IOUT	STYLE 26: PIN 1. GND 2. dv/dt 3. ENABLE 4. ILIMIT 5. SOURCE 6. SOURCE 7. SOURCE 8. VCC	STYLE 27: PIN 1. ILIMIT 2. OVLO 3. UVLO 4. INPUT+ 5. SOURCE 6. SOURCE 7. SOURCE 8. DRAIN	STYLE 28: PIN 1. SW_TO_GND 2. DASIC_OFF 3. DASIC_SW_DET 4. GND 5. V_MON 6. VBULK 7. VBULK 8. VIN
STYLE 29: PIN 1. BASE, DIE #1 2. EMITTER, #1 3. BASE, #2 4. EMITTER, #2 5. COLLECTOR, #2 6. COLLECTOR, #2 7. COLLECTOR, #1 8. COLLECTOR, #1	STYLE 30: PIN 1. DRAIN 1 2. DRAIN 1 3. GATE 2 4. SOURCE 2 5. SOURCE 1/DRAIN 2 6. SOURCE 1/DRAIN 2 7. SOURCE 1/DRAIN 2 8. GATE 1		

DOCUMENT NUMBER:	98ASB42564B	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.
DESCRIPTION:	SOIC-8 NB	PAGE 2 OF 2

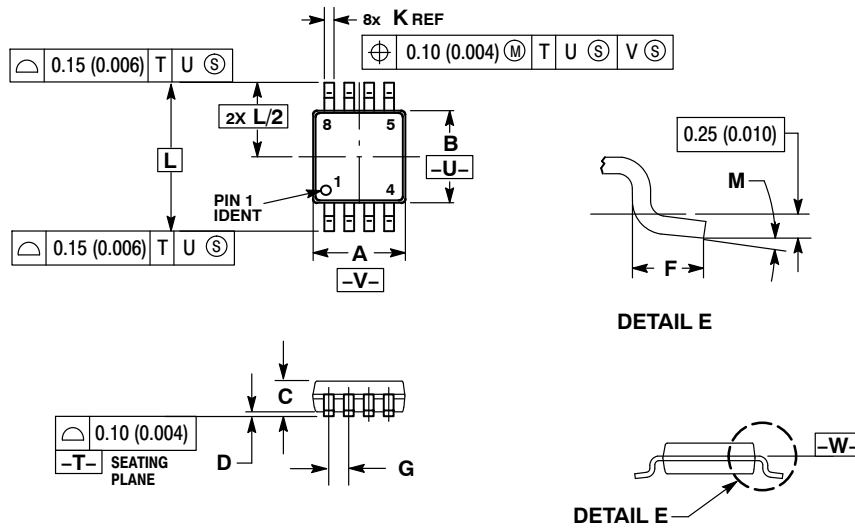
onsemi and **onsemi** are trademarks of Semiconductor Components Industries, LLC dba **onsemi** or its subsidiaries in the United States and/or other countries. **onsemi** reserves the right to make changes without further notice to any products herein. **onsemi** makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. **onsemi** does not convey any license under its patent rights nor the rights of others.



SCALE 2:1

TSSOP-8 3.00x3.00x0.95
CASE 948R-02
ISSUE A

DATE 07 APR 2000



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION A DOES NOT INCLUDE MOLD FLASH. PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
5. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
6. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	2.90	3.10	0.114	0.122
B	2.90	3.10	0.114	0.122
C	0.80	1.10	0.031	0.043
D	0.05	0.15	0.002	0.006
F	0.40	0.70	0.016	0.028
G	0.65 BSC		0.026 BSC	
K	0.25	0.40	0.010	0.016
L	4.90 BSC		0.193 BSC	
M	0°	6°	0°	6°

DOCUMENT NUMBER:	98AON00236D	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.
DESCRIPTION:	TSSOP-8 3.00x3.00x0.95	PAGE 1 OF 1

onsemi and onsemi are trademarks of Semiconductor Components Industries, LLC dba onsemi or its subsidiaries in the United States and/or other countries. onsemi reserves the right to make changes without further notice to any products herein. onsemi makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. onsemi does not convey any license under its patent rights nor the rights of others.

onsemi, **Onsemi**, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "**onsemi**" or its affiliates and/or subsidiaries in the United States and/or other countries. **onsemi** owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of **onsemi**'s product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. **onsemi** reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and **onsemi** makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using **onsemi** products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by **onsemi**. "Typical" parameters which may be provided in **onsemi** data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. **onsemi** does not convey any license under any of its intellectual property rights nor the rights of others. **onsemi** products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use **onsemi** products for any such unintended or unauthorized application, Buyer shall indemnify and hold **onsemi** and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that **onsemi** was negligent regarding the design or manufacture of the part. **onsemi** is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

ADDITIONAL INFORMATION

TECHNICAL PUBLICATIONS:

Technical Library: www.onsemi.com/design/resources/technical-documentation
onsemi Website: www.onsemi.com

ONLINE SUPPORT: www.onsemi.com/support

For additional information, please contact your local Sales Representative at
www.onsemi.com/support/sales